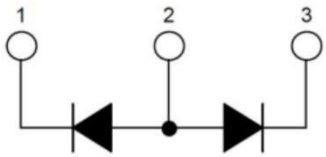
迈诺斯科技

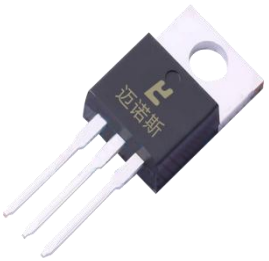
MUR1660CT

FRED
Ultrafast Soft Recovery Diode, 600V, 8A×2

Description

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery character of the diodes offers buffer in most applications. These devices are suited for power converters and other applications where the switching losses are not significant portion of the total losses.





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General Features

① Ultrafast Recovery
② 175℃operating junction temperature
③ High frequency operation
④ Low IR value
⑤ High surge capacity
⑥ Epitaxial chip construction

Application

① Freewheeling diode,snubber diode
② Uninterruptible power supplies (UPS)

Absolute Maximum Ratings						
Parameter	**Symbol**	**Test Conditions**	**Values**			**Units**
Repetitive peak reverse voltage	V_{RRM}		600			V
Continuous forward current	$I_{F(AV)}$	TA=110℃	16			A
Single pulse forward current	I_{FSM}	TA=25℃	100			A
Maximum repetitive forward current	I_{FRM}	Square wave, 20kHZ	40			A
Operating junction	T_j		175			℃
Storage temperatures	T_{stg}		-55 to +175			℃
Electrical characteristics (Ta=25℃unless otherwise specified)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Units**
Breakdown voltage Blocking voltage	V_{BR} V_R	I_R=100μA	600			V
Forward voltage	V_F	I_F=8 A		1.30	1.60	V
		I_F=8 A, Tj =125℃		1.20	1.50	V
Reverse leakage current	I_R	V_R= V_{RRM}			20	μA
		T_j=150℃, V_R=600V			200	μA
Reverse recovery time	trr	I_F=0.5A, I_R=1A, I_{RR}=0.25A			35	ns
		I_F=1A,V_R=30V, di/dt =200A/us		22	35	ns

Thermal characteristics				
Parameter	**Symbol**	**Typ.**	**Max.**	**Units**
Junction-to-Case	R_{thJC}	-	3.0	℃/W

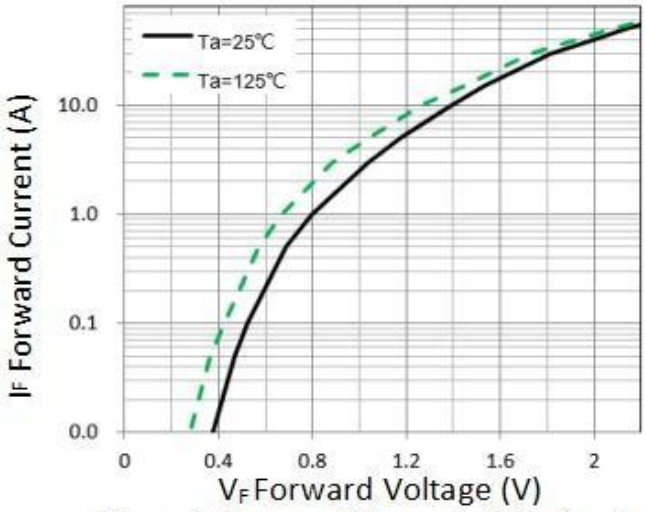


Figure 1. Forward Characteristic(typ.)

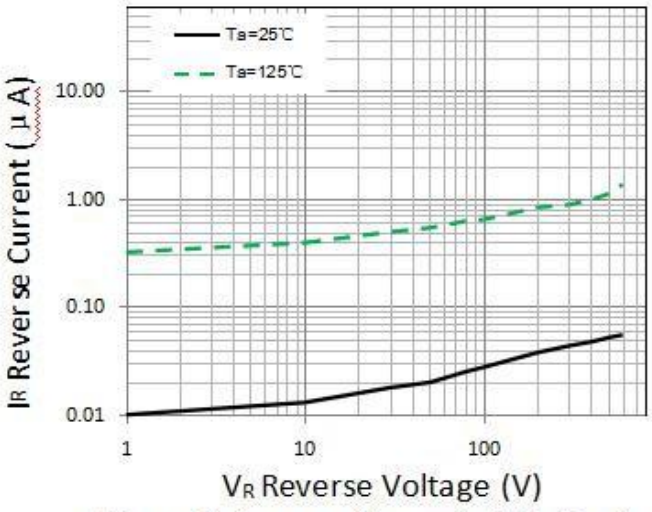
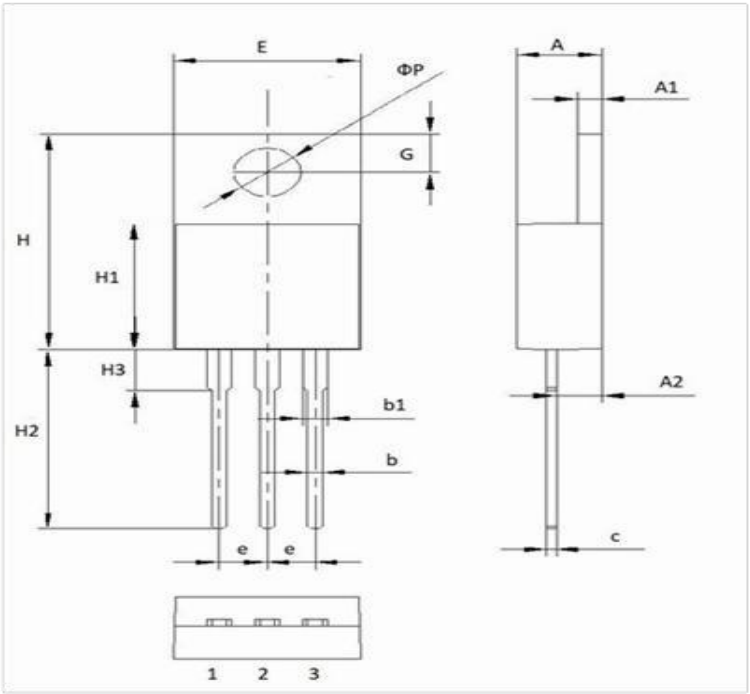


Figure 2. Reverse Characteristic (typ.)

Package Information

TO-220 PACKAGE



Symbol	Dimensions(millimeters)	
	Min.	Max.
A	4.38	4.65
A1	1.15	1.36
A2	2.35	2.85
b	0.70	0.92
b1	1.18	1.42
c	0.32	0.58
e	2.40	2.70
E	9.70	10.4
H	14.51	14.55
H1	8.40	8.80
H2	12.95	13.90
H3	3.50	3.90
G	2.50	3.00
ΦP	3.72	3.95

NOTE:

Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.

1. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
2. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
3. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change withoutprior notice.

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